

# 2SD1739

## Silicon PNP Triple-Diffused Planar Type

### Horizontal Deflection Output

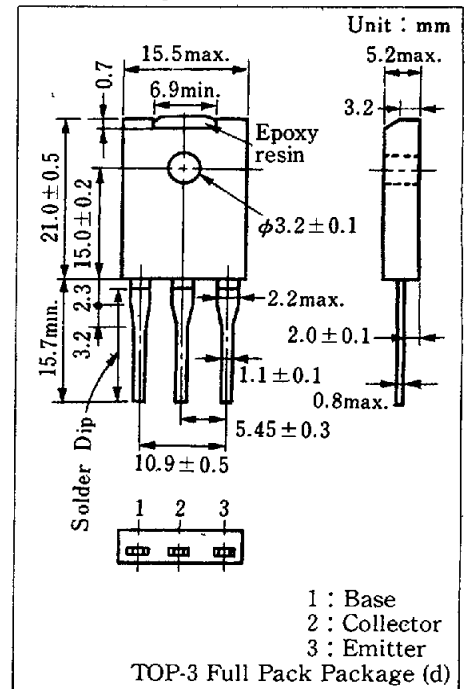
#### ■ Features

- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

#### ■ Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	$V_{CB0}$	1500	V	
Collector-emitter voltage	$V_{CES}$	1500	V	
	$V_{CEO}$	700	V	
Emitter-base voltage	$V_{EBO}$	7	V	
Peak collector current	$I_{CP}$	18	A	
Collector current	$I_C$	6	A	
Base current	$I_B$	2.5	A	
Collector power dissipation	$P_C$	Tc = 25°C	100	W
		Ta = 25°C	3	
Junction temperature	$T_j$	150	°C	
Storage temperature	$T_{stg}$	-55 ~ +150	°C	

#### ■ Package Dimensions



#### ■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB}=750\text{ V}, I_E=0$			10	$\mu\text{A}$
		$V_{CB}=1500\text{ V}, I_E=0$			1	mA
Emitter-base voltage	$V_{EBO}$	$I_E=1\text{ mA}, I_C=0$	7			V
DC current gain	$h_{FE}$	$V_{CE}=5\text{ V}, I_C=1\text{ A}$	6		30	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=5\text{ A}, I_B=1.2\text{ A}$			8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=5\text{ A}, I_B=1.2\text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE}=10\text{ V}, I_C=1\text{ A}, f=0.5\text{ MHz}$		2		MHz
Storage time (L load)	$t_{stg}$	$I_C=5\text{ A}, I_{B1}=1.2\text{ A}$			10	$\mu\text{s}$
Fall time (L load)	$t_f$	$I_{B2}=-1.2\text{ A}, L_B=5\text{ }\mu\text{H}$			0.8	$\mu\text{s}$
Storage time (R load)	$t_{stg}$	$I_C=5\text{ A}, I_{B1}=1\text{ A}$		1.5		$\mu\text{s}$
Fall time (R load)	$t_f$	$I_{B2}=-2\text{ A}, V_{CC}=200\text{ V}$		0.2		$\mu\text{s}$

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